

Clean Version Of Amended Claims

SD 34 34. (thrice amended) A method for fabricating an interconnect for a semiconductor component having a bumped contact comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of leads on the surface configured to electrically engage and support the bumped contact and a connecting segment on the surface configured to electrically connect the leads to one another;

forming a recess in the surface such that the leads cantilever over the recess and are configured for movement within the recess during electrical engagement of the bumped contact;

forming a conductive via in the substrate in electrical communication with the connecting segment; and

forming a contact on the opposing surface in electrical communication with the conductive via.

35. (thrice amended) The method of claim 34 wherein the forming the conductive via step comprises forming an opening through the connecting segment and the substrate and forming a conductive material in the opening.

SD 38 38. (thrice amended) The method of claim 34 further comprising forming blades on the leads configured to penetrate the bumped contact.

SD 39 39. (thrice amended) A method for fabricating an interconnect for a semiconductor component having a bumped contact comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of leads on the surface configured to electrically engage and support the bumped contact and a

connecting segment on the surface configured to electrically connect the leads to one another;

forming a recess in the surface such that the leads are cantilevered over the recess and are configured to move within the recess during electrical engagement of the bumped contact;

forming an opening through the substrate and the connecting segment;

forming a conductive material in the opening; and

forming a contact on the opposing surface in electrical communication with the conductive material.

D3
40. (thrice amended) The method of claim 39 wherein the forming the opening step comprises laser machining.

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41. (thrice amended) The method of claim 39 wherein the recess is generally square having four sides and the leads extend generally orthogonally to the four sides.

42. (twice amended) The method of claim 39 further comprising shaping the leads with a radius of curvature corresponding to a diameter of the bumped contact.

43. (thrice amended) The method of claim 39 further comprising forming a plurality of blades on the leads configured to penetrate the bumped contact.

D5
49. (twice amended) A method for fabricating an interconnect for a semiconductor component having a plurality of bumped contacts comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of interconnect contacts on the substrate configured to electrically engage the bumped contacts, each interconnect contact comprising a recess in the surface and a plurality of leads cantilevered over the

recess configured to support a bumped contact for movement in the recess;

forming a plurality of conductive vias in the substrate in electrical communication with the interconnect contacts; and

forming a plurality of contacts on the opposing surface having a different pitch than that of the interconnect contacts.

50. (twice amended) The method of claim 49 wherein the contacts comprise pads.

51. (twice amended) The method of claim 49 further comprising forming a plurality of blades on the leads configured to penetrate the bumped contact.

52. (twice amended) The method of claim 49 wherein the forming the conductive vias step comprises laser machining.

53. (amended) A method for fabricating an interconnect for a semiconductor component having a bumped contact comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of leads on the surface configured to electrically engage the bumped contact;

forming a connecting segment on the surface electrically connecting the leads;

forming a recess in the surface with the leads cantilevered over the recess and configured to support the bumped contact for movement within the recess;

shaping the leads with a radius of curvature corresponding to a diameter of the bumped contact;

forming a conductive via in the substrate in electrical communication with the connecting segment; and

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forming a contact on the opposing surface in electrical communication with the bumped contacts.

54. (amended) The method of claim 53 further comprising forming a plurality of blades on the leads configured to penetrate the bumped contact.

55. (amended) The method of claim 53 wherein the forming the conductive via step comprises laser machining an opening through the connecting segment and the substrate.

56. (amended) The method of claim 53 wherein the contact comprises a pad.

57. (amended) The method of claim 53 wherein the forming the conductive via step comprises electrically insulating and then at least partially filling an opening with a conductive material.

58. (amended) The method of claim 53 wherein the substrate comprises a material selected from the group consisting of silicon, ceramic and plastic.

Concluded
